




Precursor concentration-tuned optical and electrochromic performance of sol-gel-derived V₂O₅ thin-film devices

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ABSTRACT

Electrochromic (EC) devices have gained significant attention in energy-saving applications, with V₂O₅ standing out owing to its excellent Li-ion intercalation and multi-color properties compared to the widely used WO₃. Nonetheless, no research has addressed the effect of V₂O₅ concentration on EC performance. Given the rising popularity of V₂O₅ in EC devices, this observation has indicated a significant research gap that should be addressed. Therefore, this study investigated the performance of V₂O₅ EC devices with concentrations ranging between 0.02 mol/L and 0.1 mol/L via sol-gel spin coating. Consequently, higher film thickness was observed as the sol-gel concentration increased, as the V₂O₅ thin films transformed from amorphous to crystalline phases. Increasing grain size with worm-like structures was also observed as the concentration increased. The EC device that balanced between optical modulation (OM), coloration efficiency (CE), and coloring (*t_c*) with bleaching times (*t_b*) was then observed for the ITO/0.08 V₂O₅/electrolyte/ITO device. This device showcased optimized values for OM (37.11 %), CE (26.53 cm² C⁻¹), *t_c* (7 s), and *t_b* (14 s). Overall, these findings could provide novel information regarding the correlation of V₂O₅ concentration and EC device performance. A unique contribution was also presented in this study by demonstrating a direct relationship between the concentration of sol-gel precursors, the evolution of structure, and the EC performance, potentially for large-scale production and energy-efficient smart window technologies.

1. Introduction

Switchable smart glass technology has been widely explored for its potential to reduce energy consumption in many environments. The technology is also increasingly used in buildings as it can block ultraviolet (UV) and infrared (IR) light while minimizing the reliance on artificial lighting, effectively reducing heat gain and loss, protecting interiors, and offering on-demand privacy [1]. These functionalities allow smart glass to be versatile and can be integrated into homes and vehicles [2]. Therefore, research on electrochromic (EC) devices is driven by their unique ability to change optical properties with an applied voltage, leading to diverse applications including smart

windows or coupled with batteries [3,4].

The common EC materials used today include TiO₂, WO₃, and V₂O₅ owing to their high coloration efficiency (CE), optical modulation (OM), versatility in preparation and application, and structural stability [5,6]. In 1930, Kobosew and Nekrassov discovered that WO₃ powders could undergo coloration by reduction in an acidic solution, making WO₃ one of the earliest documented EC technologies [7]. Nonetheless, several limitations affect the performance of EC devices. WO₃ can only exhibit a dark blue color and has limited modulation capabilities [8,9]. Likewise, V₂O₅ presents multi-color EC display capability, including orange, green, and blue, making it suitable for diverse display applications [10]. In its most stable phase, V₂O₅ undergoes reversible redox reactions

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involving Li-ion intercalation and deintercalation to achieve multi-color transitions [11]. These reactions alter the oxidation state of V and modify the optical features of a material, leading to different colors. The reaction is described as follows [12]:



The performance of these devices is crucial for their practical applications. Numerous performance metrics include OM, switching speed, CE, and stability [13,14]. These performance metrics highly depend on the fabrication process [15], such as the thickness [16], and particularly for the sol-gel method, the sol concentration. Various studies focus on material design for V_2O_5 EC devices. For example, Panagopoulou et al. reported that W doping in V_2O_5 enhanced CE [17]. Although increasing attention towards V_2O_5 thin films is observed, there is no work focusing on the impact of sol-gel concentration on EC device performance.

The viscosity, precursor ratio, and hydrolysis-condensation kinetics of a solution are dependent on its sol-gel concentration. In turn, the concentration determines film thickness, porosity, crystallinity, and stoichiometry after annealing. Structural and morphological features of a film can then determine the degree of ion-diffusion-limited charge storage and the OM performance in EC devices [18,19]. Thus, balanced optical contrast, CE, and cycling stability in V_2O_5 -based EC systems require well-tailored sol-gel concentrations. Much research on the EC properties of the V_2O_5 also primarily focused on the thin film level under controlled conditions. This approach neglects the crucial step of investigating real-world applications of practical devices, such as the sol-gel method.

According to the authors' understanding, previous studies did not examine how V_2O_5 sol-gel concentration influenced EC performance (EC device rather than film properties). In this study, the novelty was found within the thorough examination of sol-gel precursor concentration as a crucial processing factor, alongside demonstrating its direct relationship with structural development and EC performance (OM, ion diffusion behavior, and switching kinetics). From an application perspective, scalable fabrication and optimization of V_2O_5 -based EC devices could also be accomplished for smart window and energy-efficient building applications [20,21].

This study fabricated V_2O_5 thin films (0.02–0.10 mol/L) using the sol-gel spin coating approach and assembled them into EC devices using lithium perchlorate ($LiClO_4$) as the electrolyte. The device structure selected in this study was indium tin oxide (ITO)/ V_2O_5 /electrolyte/ITO. The devices then underwent X-ray diffraction (XRD), field-emission scanning electron microscopy (FESEM), cyclic voltammetry (CV), chronoamperometry (CA), energy-dispersive X-ray spectroscopy (EDX), and UV-Vis spectroscopy to investigate their performance based on structural and optical characteristics. Collectively, this study demonstrated an approach to optimize the performance of V_2O_5 -based EC devices via sol-gel spin coating.

2. Materials and methods

2.1. Materials

This work acquired several chemicals from Sigma-Aldrich, Rockville, MD, USA, including acetonitrile (ACN), 30 % hydrogen peroxide (H_2O_2), V_2O_5 powder, $LiClO_4$, propylene carbonate (PC), and polymethylmethacrylate (PMMA). All chemicals were utilized as acquired, without needing additional purification.

2.2. Synthesis of the V_2O_5 Sol-Gels

Fig. 1 depicts the step-by-step process of the sol-gel fabrication for V_2O_5 . This sol-gel preparation involved adding 15 ml of H_2O_2 (30 %) to deionized water (15 ml). The mixture was stirred for 10 mins at ambient temperature prior to adding 0.5456 g of V_2O_5 powder. This mixture was immediately stirred at 70°C for 6 mins, and the exothermic reaction occurred. The mixture was then stirred for another 3 mins, in which a dark red solution was obtained. Subsequently, four separate solutions were prepared by diluting 4 ml, 3 ml, 2 ml, and 1 ml of the solutions with 1 ml, 2 ml, 3 ml, and 4 ml of DI water to obtain 0.08 mol/L, 0.06 mol/L, 0.04 mol/L, and 0.02 mol/L solutions, respectively. The sol-gels were finally kept in their respective glass vials and aged for at least 48 h.

2.3. Preparation of the ITO/ V_2O_5 /electrolyte/ITO EC devices

The sol-gel was spin-coated using indium tin oxide (ITO) substrates based on sol-gel spin coating at 3000 rpm. This process was repeated five times on an active area of 2.4 cm² to achieve five layers of V_2O_5 . The films were then immediately annealed at 200°C (1 h). Subsequently, the V_2O_5 -based EC device was assembled and sealed with UV resin to contain the gel electrolyte. This study fabricated the Li^+ gel electrolyte following the methodology adapted from our previous work [22]. In brief, the electrolyte was prepared by combining PC [50 % v/v (12.5 ml)], $LiClO_4$ [1 M (2.6598 g)], and PMMA [28 % w/v (7 g)] in a 25 ml ACN solution. This mixture was stirred at a medium speed for 24 h. The mixture was then baked at 90°C for 1 h to produce a highly viscous gel-like solution. Lastly, the V_2O_5 -based EC devices prepared in this study contained 0.02 mol/L, 0.04 mol/L, 0.06 mol/L, 0.08 mol/L, 0.10 mol/L of V_2O_5 : (i) ITO/0.02 V_2O_5 /electrolyte/ITO, (ii) ITO/0.04 V_2O_5 /electrolyte/ITO, (iii) ITO/0.06 V_2O_5 /electrolyte/ITO, (iv) ITO/0.08 V_2O_5 /electrolyte/ITO, and (v) ITO/0.10 V_2O_5 /electrolyte/ITO.

2.4. Characterization tools

The analysis concerning the V_2O_5 thin films was carried out via an XRD instrument (Shimadzu) employing Cu $K\alpha$ radiation ($\lambda = 1.540598 \text{ \AA}$), with measurements taken across a 2θ range of 20° to 60°. Surface morphology and cross-sectional views were also assessed via a

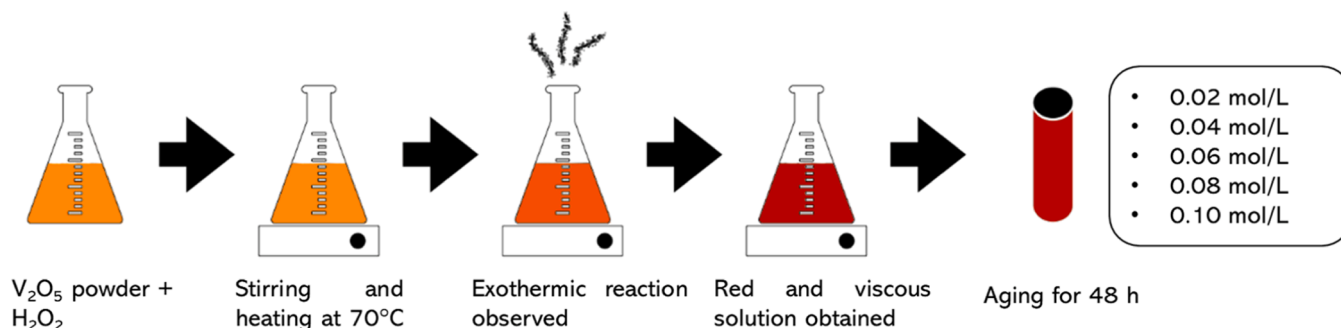


Fig. 1. The fabrication process of the V_2O_5 sol-gels (0.02–0.10 mol/L).

FESEM tool (Nova NanoSEM 450). Meanwhile, elemental composition was assessed using an EDX spectrometer (Oxford Instruments). Optical transmittance measurements were then taken with the UV-Vis spectrophotometer (Avantes AvaSpec-2048L). Finally, the EC properties regarding the V_2O_5 -based EC devices containing between 0.02 mol/L and 0.10 mol/L of V_2O_5 were evaluated using CA and CV techniques (Autolab PGSTAT204).

3. Results and Discussion

3.1. Structural properties of V_2O_5 thin films

Fig. 2 portrays the XRD outcomes of V_2O_5 films deposited at 0.02 mol/L to 0.10 mol/L. Only diffraction peaks representing the (222) and (400) planes of the ITO substrate were observed at 30.2° and 35.2° for the 0.02 mol/L and 0.04 mol/L V_2O_5 thin films (ICDD no. 06-0416) [23]. The characteristic diffraction peaks of V_2O_5 were also not present, suggesting that the films were amorphous. Nevertheless, weak peaks denoting the (110) plane of orthorhombic V_2O_5 were observed at 24.7° for the 0.06 mol/L V_2O_5 film, indicating some crystalline nature. This (110) plane of orthorhombic V_2O_5 then grew more intense with rising concentration from 0.06 mol/L to 0.10 mol/L, while weak (011) and (002) planes of orthorhombic V_2O_5 were observed for the 0.08 mol/L and 0.10 mol/L V_2O_5 thin films (ICDD no. 01-089-0612) [24,25]. Interestingly, there was a strong and sharp peak representing the (001) plane of orthorhombic V_2O_5 at 20.3° for the 0.10 mol/L V_2O_5 film. This peak was not present for V_2O_5 thin films deposited at other concentrations, implying a high crystallinity for the 0.10 mol/L V_2O_5 film.

This increasing trend of characteristic peak intensities could be understood by measuring the grain size (D_g) of the V_2O_5 . The values can be computed using Scherrer's formula, which is provided as follows [26]:

$$D_g = (0.9\lambda) / (\text{FWHM} \times \cos\theta) \quad (2)$$

where λ denotes the X-ray wavelength; FWHM denotes the full width at half maximum of the diffraction peak; and θ denotes the half of the diffraction angle (Bragg angle). Table 1 tabulates the average D_g of the various samples calculated using the (110) plane, in which there are no peaks observed for the 0.02 and 0.04 mol/L V_2O_5 films. Therefore, their average D_g could not be calculated. For the other films, there was a corresponding rise in the number of available nuclei and the density of the deposited layers with a larger precursor solution content in the sol-gel process. This process seemed to promote more effective atomic rearrangement during the annealing process, leading to improved crystal growth [27,28]. Thus, the increasing trend of D_g observed for 0.06 mol/L, 0.08 mol/L, and 0.10 mol/L V_2O_5 films was validated.

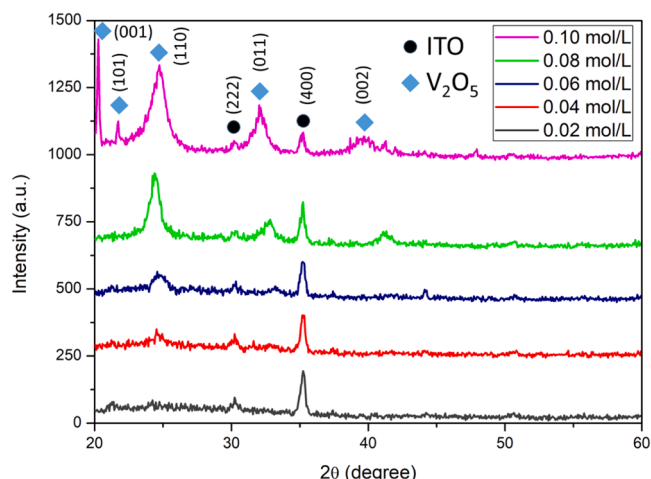


Fig. 2. The XRD spectra of V_2O_5 films deposited at 0.02 mol/L to 0.10 mol/L.

Table 1

Summary of the average D_g values obtained for the V_2O_5 films deposited at 0.02 mol/L to 0.10 mol/L.

Concentration (mol/L)	D_g (nm)
0.02	- ^a
0.04	- ^a
0.06	13.6
0.08	18.1
0.10	67.3

^a No peaks observed for the (110) plane.

Fig. 3 portrays the cross-sectional FESEM images concerning V_2O_5 films fabricated from 0.02 mol/L to 0.10 mol/L. The images implied that as higher sol-gel concentrations were used, film thickness was higher, which was consistent with findings in the literature on thin films synthesized based on the sol-gel approach [29]. Notable increase in thickness was also observed, rising from 291 nm to 699 nm with rising concentration (0.08–0.10 mol/L). Specifically, the thickness obtained in this study aligned closely with those documented in existing literature for V_2O_5 films produced at comparable concentrations, affirming the reliability of the current findings [22]. The optical properties section below presents a more detailed discussion on the relationship between thickness and optical transmittance, noting that a similar trend of decreasing transmittance has been observed in other studies [22,30].

It could be observed that with an increase in precursor concentration, the V_2O_5 film produced at 0.06 mol/L was somewhat thinner than that at 0.04 mol/L. Both dynamics of spin-coating, alongside the structural changes that occurred during post-annealing, were probably the cause of this effect [31]. As previously mentioned in the XRD analysis, the 0.04 mol/L film was predominantly amorphous, while improved crystallinity was then recorded for the 0.04 mol/L film (see Fig. 2). This higher crystallinity could be ascribed to the greater extent of network condensation and densification processes occurring during annealing. Certain sol-gel-related studies also reported that as the amorphous network transitioned into a more compact crystalline arrangement, a decrease in film volume perpendicular to the substrate could occur from both processes [32–34]. As such, even when the precursor molarity was higher, a thinner final film at intermediate concentrations was obtained during spin coating owing to densification (amorphous \rightarrow crystalline).

Fig. 4 portrays the top-view FESEM images of the V_2O_5 films fabricated at 0.02 mol/L to 0.10 mol/L. The morphological properties of the films were characterized by FESEM at 50,000 times magnification using a through-lens detector, alongside a 10.00 kV accelerating voltage (working distance = 5.2 mm). Rather than changes in imaging parameters, differences in surface appearance arose from intrinsic morphological variations among the films. At 0.02 mol/L, the V_2O_5 film appeared to have a relatively uniform morphology with fine-grained structure. As the concentration increased (0.04 mol/L), the texture on the surface became more pronounced. Surprisingly, worm-like structures began to form at 0.06 mol/L. At 0.10 mol/L, the diameter grew to around 10 times the previous size. This outcome could be explained by the increase in the electrostatic forces between solute particles as the solute concentration rose, causing the formation of larger grains [29]. Table 2 then lists the average diameter (D_a) of the worm-like structures observed on the thin films.

3.2. Elemental composition of V_2O_5 thin films

Fig. 5 depicts the elemental composition of the V_2O_5 films at 0.02 mol/L to 0.10 mol/L determined by EDX. The EDX spectra confirmed the expected elements of V, O, In, and Sn. At lower concentrations (0.02–0.06 mol/L), stronger In and Sn peaks were observed due to thinner V_2O_5 films. Thicker films then suppressed substrate signals at higher concentrations (0.08–0.10 mol/L), emphasizing V and O.

Table 3 lists the atomic percentage of V_2O_5 films prepared at

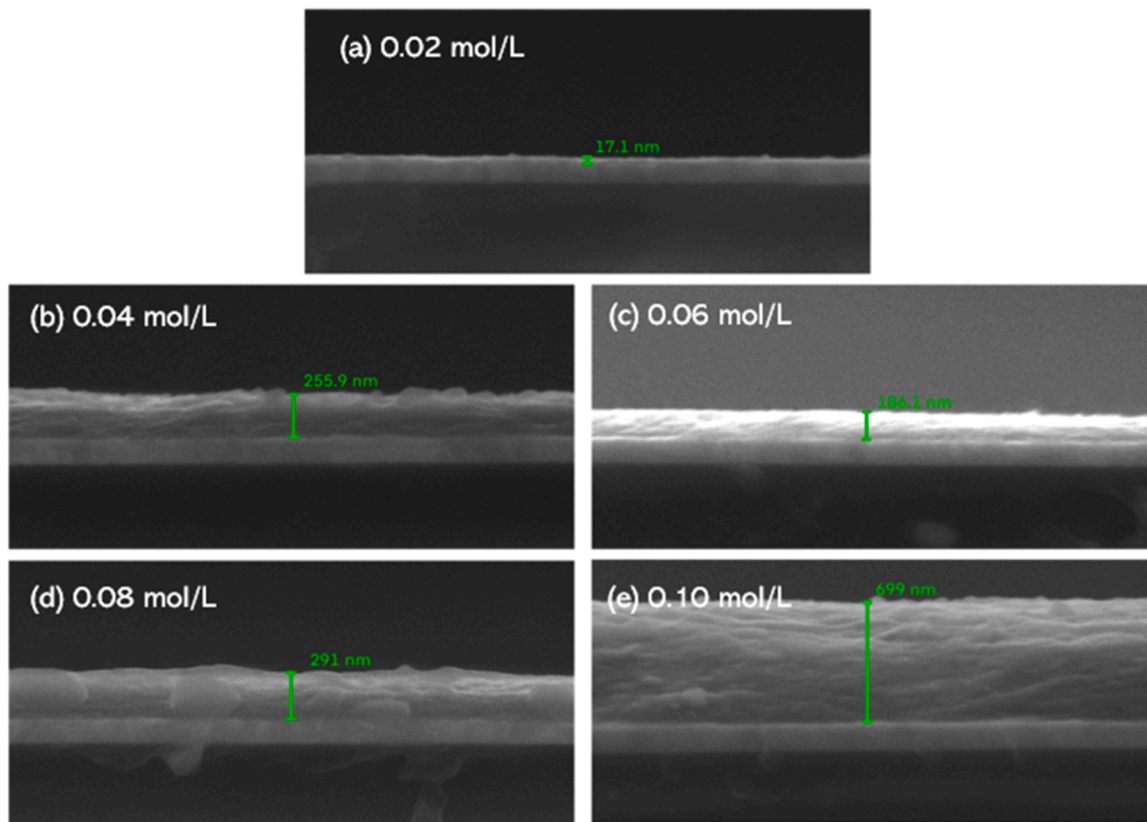


Fig. 3. The cross-section FESEM images reveal the thickness of V_2O_5 thin films at (a) 0.02 mol/L, (b) 0.04 mol/L, (c) 0.06 mol/L, (d) 0.08 mol/L, and (e) 0.10 mol/L.

different concentrations. As concentration increased, the atomic percentage of V increased while O decreased. This trend occurred because the increasing thickness reduced the O signal from the substrate. With the rising film thickness, the detection of the substrate's O signal diminished while the measurement of the film's V intensified, changing the atomic percentage [35]. This observation could also be attributed to kinetically limited oxidation caused by rapid deposition [36]. When the film was deposited at an accelerated rate, oxygen might not have sufficient time to diffuse throughout all areas, leading to incomplete oxidation and an elevated V-to-O ratio.

For the atomic ratios of V_2O_5 0.08 mol/L and 0.10 mol/L samples, the observed discrepancies could be attributed to the EDX quantification limitations for oxides [37]. Rather than indicating the existence of a secondary phase, diminished sensitivity for lighter elements (including oxygen) might occur for EDX as a semi-quantitative method due to several reasons, such as low X-ray counts and differential absorption [38,39]. Particularly, no additional crystalline phases present beyond orthorhombic V_2O_5 were demonstrated from the XRD results (see Fig. 2). Hence, the films were inferred to maintain phase purity, and any observed deviations in stoichiometry were likely due to measurement deviations.

3.3. Optical characteristics of V_2O_5 thin films

Fig. 6 presents the virgin film transmittance spectra of V_2O_5 films deposited at 0.02 mol/L to 0.10 mol/L. Increased sol-gel concentration corresponded to larger particle size and an elevated defect or impurity state density. These alterations diminished quantum confinement and generated mid-gap states. Therefore, the edge of the transmittance curve shifted towards longer wavelengths, indicating a reduced effective bandgap [40]. Also, there was a greater decrease in transmittance at longer wavelengths as precursor concentration was increased. This outcome might be due to greater concentration, which increased surface

roughness and D_g , leading to greater light scattering. Accordingly, transmittance was reduced more within the longer wavelength region. This type of transmittance and thickness dependence was also observed in V_2O_5 films, which, when thickened, continuously led to a transmittance drop in all wavelength regions [41].

As V_2O_5 concentration increased, the observed red shift within the absorption edge was qualitatively linked to the defect-related states within the bandgap. In transition-metal oxides processed through sol-gel methods, the presence of structural disorder, oxygen vacancies, and mixed valence states (V^{4+}/V^{5+}) was recognised to create localised mid-gap states. Hence, towards lower photon energies, the broadening of the absorption tail could be observed. Typically, defect-induced band tailing appears as a red shift within the absorption edge, accompanied by increased sub-bandgap absorption [12,42]. Although this study did not include a quantitative Urbach energy or Tauc analysis, the optical behaviour observed aligned with defect-assisted absorption mechanisms that were extensively documented for sol-gel-derived V_2O_5 and other oxide EC films [43–45].

3.4. EC properties of the ITO/ V_2O_5 /electrolyte/ITO EC devices

Fig. 7 presents the CV and diffusion coefficient (D_c) graphs of the ITO/ V_2O_5 /electrolyte/ITO EC devices for different V_2O_5 concentrations. The CV measurements were performed between -2 V and 2.5 V (scan rate = 0.1 V/s). These CV curves showed cathodic and anodic peaks, indicating that the reaction was a reversible redox process involving charge insertion and extraction. With larger V_2O_5 concentrations from 0.02 mol/L to 0.10 mol/L, the cathodic peak current (i_p) rose from -0.49 mA to -1.83 mA (see Table 4). This finding demonstrated that the increasing concentration of V_2O_5 contributed to the number of charge insertions.

The results obtained from the CV measurements are employed to compute the D_c for the Li^+ ions based on the Randles-Sevcik equation as

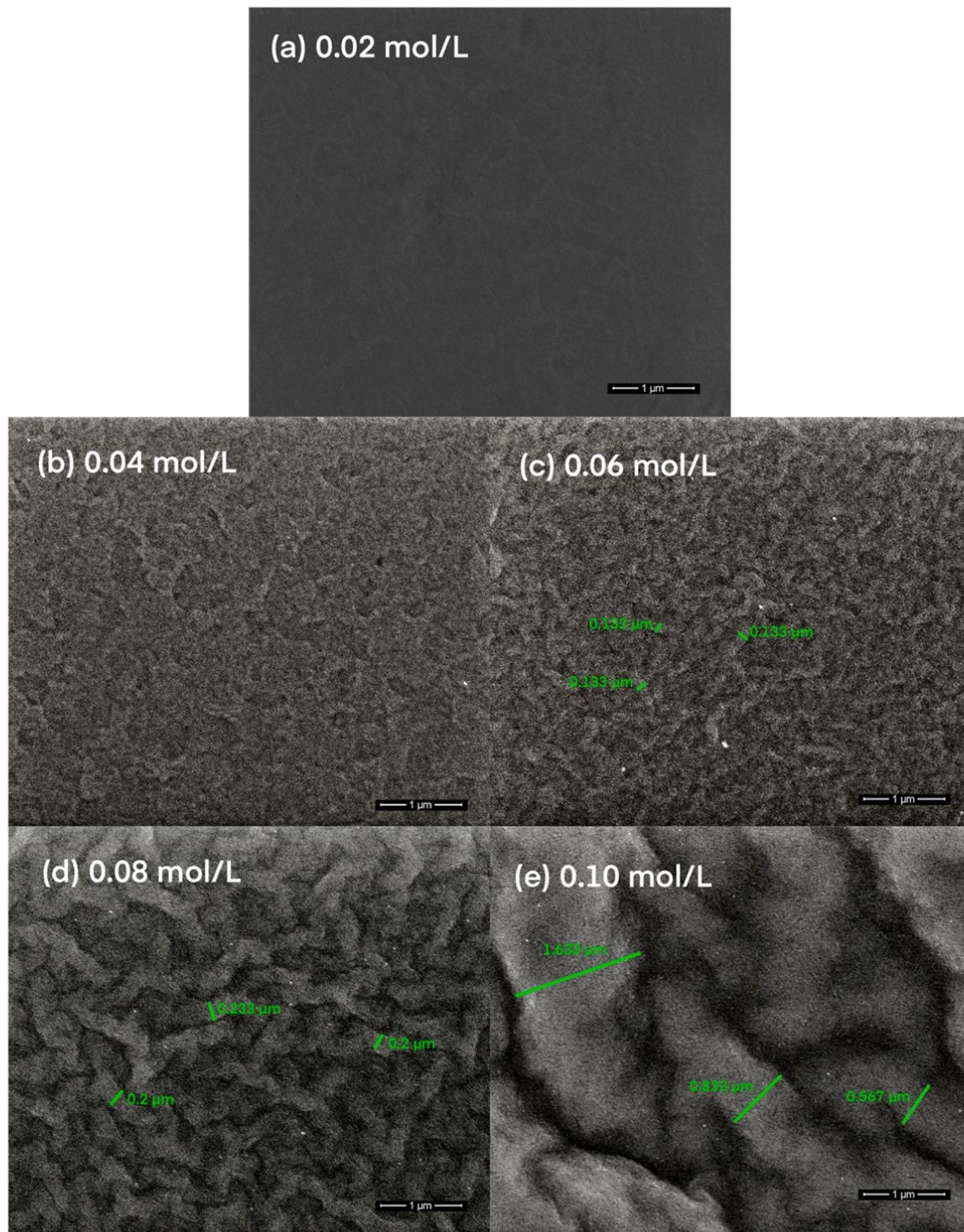


Fig. 4. The top-view FESEM images of V_2O_5 films fabricated at (a) 0.02 mol/L, (b) 0.04 mol/L, (c) 0.06 mol/L, (d) 0.08 mol/L, and (e) 0.10 mol/L. Selected D_c measurements are presented in these images.

follows [46]:

$$i_p = 2.69 \times 10^5 \times A \times n^{\frac{3}{2}} \times D_c^{\frac{1}{2}} \times C_o \times v^{\frac{1}{2}} \quad (3)$$

where n represents the number of electrons transferred within the redox reaction (1); C_o represents the electrolyte concentration; A represents the electrode surface area; and v represents the scan rate. Fig. 7(c) also provides a schematic representation of the EC mechanism within the ITO/ V_2O_5 /electrolyte/ITO device. This mechanism involved the

reversible insertion and extraction of Li^+ ions, which was coupled with the V^{5+}/V^{4+} redox mechanism, leading to the cathodic and anodic characteristics evident in the CV curves.

The ITO/0.10 V_2O_5 /electrolyte/ITO device demonstrated the highest D_c of $7.86 \times 10^{-17} \text{ cm}^2 \text{ s}^{-1}$. This observation was due to the more porous film structure at higher concentration, providing a shorter diffusion path length that allowed ions to move quickly into the EC layer [47,48]. Meanwhile, the ITO/0.02 V_2O_5 /electrolyte/ITO device showed the lowest D_c of $0.56 \times 10^{-17} \text{ cm}^2 \text{ s}^{-1}$. This observation could be

Table 2

Summary of the D_a values of the worm-like structures on V_2O_5 thin films deposited at various concentrations at 0.02 mol/L to 0.10 mol/L.

Concentration (mol/L)	D_a (μm)
0.02	- ^a
0.04	- ^a
0.06	0.134 ± 0.004
0.08	0.211 ± 0.019
0.10	0.943 ± 0.273

^a D_a cannot be calculated due to the FESEM tool's capability at maximum magnification.

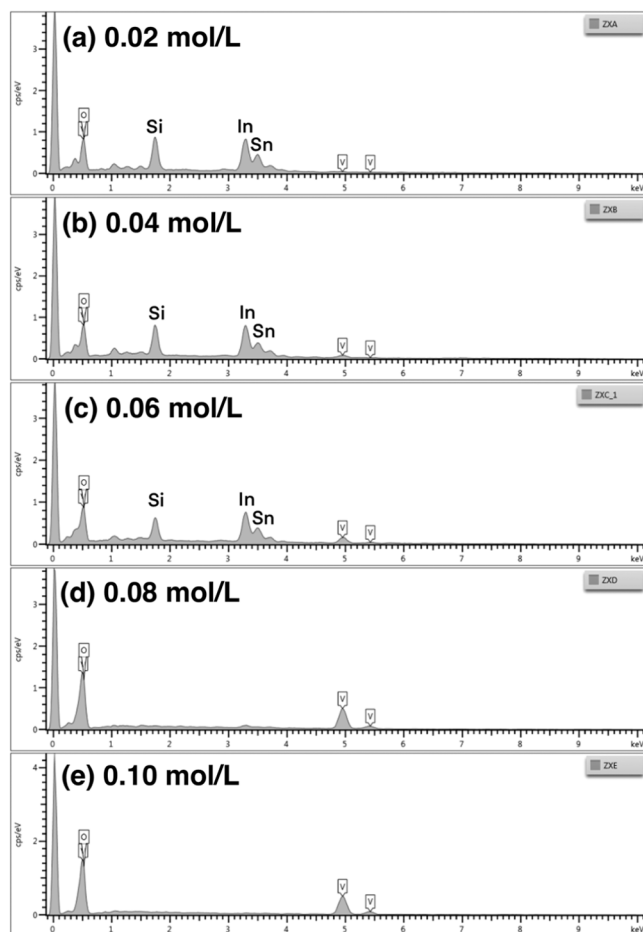


Fig. 5. The EDX results of V_2O_5 films fabricated at (a) 0.02 mol/L, (b) 0.04 mol/L, (c) 0.06 mol/L, (d) 0.08 mol/L, and (e) 0.10 mol/L.

Table 3

Summary of the elemental composition of V_2O_5 films deposited at 0.02 mol/L to 0.10 mol/L.

Concentration (mol/L)	Atomic Ratio (%)	
	V	O
0.02	5.36	94.64
0.04	17.39	82.61
0.06	34.88	65.12
0.08	70.86	29.14
0.10	70.19	29.81

attributed to the less porous film structure at lower concentration, having a longer diffusion path length for more ions to move into the EC layer. The D_c values obtained by all the ITO/ V_2O_5 /electrolyte/ITO

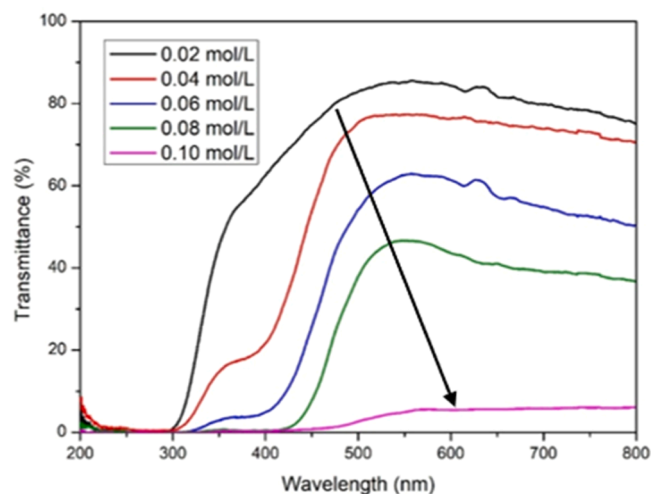


Fig. 6. The virgin transmittance spectra of the V_2O_5 thin films at 0.02 mol/L to 0.10 mol/L.

devices were also consistent with devices fabricated using the sol-gel method [47,49]. Notably, a higher D_c as concentration increased indicated a faster kinetic response and revealed a higher ion diffusivity. The more extensive layer under the CV graph also showed the larger charge capacity of the EC devices as concentration increased [30].

Fig. 8 depicts the CA measurements of the ITO/ V_2O_5 /electrolyte/ITO EC devices for different V_2O_5 concentrations (step potential = $-2\text{ V} - 2.5\text{ V}$, 60 s). Following this process, UV-vis spectroscopy was utilized to assess the transmittance of the V_2O_5 EC devices (wavelength = 633 nm). This data demonstrated the OM capability (ΔT), which can be computed in this study as follows:

$$\Delta T(\%) = T_b(\%) - T_c(\%) \quad (4)$$

where T_c and T_b denote the bleaching and coloring transmittances, respectively.

Fig. 8(f) illustrates that as the concentration increases, the OM elevates but reaches saturation at 0.08 mol/L. At this point, the OM then decreased for the ITO/0.10 V_2O_5 /electrolyte/ITO device. This trend was likely attributed to the thickness effect, which increased with sol-gel concentration as confirmed by the FESEM images [22,30]. Notably, the drop in OM was ascribed to the rough surface and higher D_g of the V_2O_5 film fabricated at a larger concentration, which impeded ion diffusion [50]. The D_g was also the highest for the 0.10 mol/L V_2O_5 films, revealing large worm-like structures. Likewise, the decrease in overall transmittance likely contributed to the suppression in OM, which was reported by other researchers [49,50].

Table 5 compares the difference between T_c and T_b of the ITO/ V_2O_5 /electrolyte/ITO EC devices at various concentrations. The results denoted that T_c and T_b decreased with rising concentration, owing to the higher light scattering properties of the thin film as surface roughness increased (higher concentration) [51,52]. The ITO/0.08 V_2O_5 /electrolyte/ITO EC device also exhibited the highest OM of 37.11%. Nevertheless, this value declined for ITO/0.10 V_2O_5 /electrolyte/ITO (19.18%), which might be caused by ion-trapping when Li ions were injected into the film at high concentrations [53].

When comparing the FESEM cross-sections (170–699 nm), correlations were observed between thickness, optical transmittance, and ΔT . For EC oxides, greater optical absorption and optical density (OD) could be accomplished when the films became thicker, alongside a change from amorphous to crystalline structure [45]. Nevertheless, when exceeding an optimal range, bleached-state transmittance and OM might reduce due to increased baseline absorption or scattering (even though charge storage could improve) [54]. Thus, when the concentration was

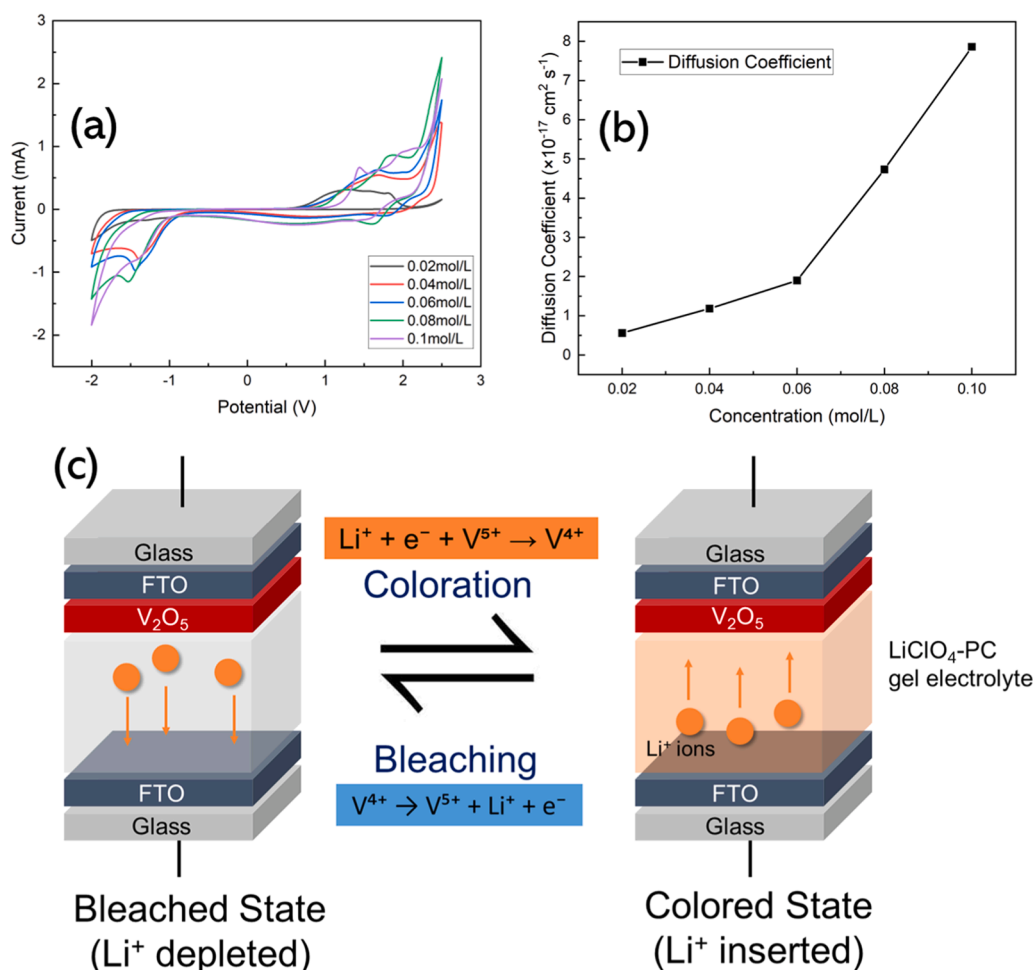


Fig. 7. (a) The CV graphs and (d) D_g values of the ITO/ V_2O_5 /electrolyte/ITO EC devices fabricated at various sol concentrations. (c) Schematic of Li^+ intercalation/deintercalation and the corresponding $\text{V}^{5+}/\text{V}^{4+}$ redox mechanism governing coloration and bleaching.

Table 4

Summary of the D_c values obtained for the ITO/ V_2O_5 /electrolyte/ITO EC devices at 0.02 mol/L to 0.10 mol/L.

Device	i_p (mA)	$D_c (\times 10^{-17} \text{ cm}^2 \text{ s}^{-1})$
ITO/0.02 V_2O_5 /electrolyte/ITO	-0.49	0.56
ITO/0.04 V_2O_5 /electrolyte/ITO	-0.71	1.18
ITO/0.06 V_2O_5 /electrolyte/ITO	-0.90	1.90
ITO/0.08 V_2O_5 /electrolyte/ITO	-1.42	4.73
ITO/0.10 V_2O_5 /electrolyte/ITO	-1.83	7.86

further increased to 0.10 mol/L, ΔT decreased to 19.18 %, despite continued film thickening. Previous studies also documented the trade-off between thickness and optical properties for WO_3 films, indicating that the modulation of transmittance was significantly influenced by thickness [54,55]. As such, maximising ΔT could be attained at an optimal intermediate thickness.

Generally, CE is a critical variable in the performance of EC devices. This parameter is a measure of how effectively the EC device can undergo color change with the intercalation of an electric charge and is denoted as the change in OD per unit charge density (Q_A), which is computed as follows [56]:

$$CE = \frac{\Delta(OD)}{Q_A} = \frac{\log\left(\frac{T_b}{T_c}\right)}{Q_A} \quad (5)$$

where Q_A represents the intercalated charge per unit area. Fig. 9(a) then

illustrates that the CE saturates at around 0.06 mol/L, which is attributed to high OM. Fig. 9(b) also displays the correlation between OD and Q_A .

Within an EC device, increasing the inserted charge increased the number of sites switched, which in turn elevated OD, but only to the extent that most of the film was modulated. Beyond this, modulated charge produced increasingly fewer returns, which was the reason for the increase in the CE. These CE and charge characteristics were also observed in other metal oxide-related studies, supporting this observation [57]. In contrast, it was apparent from the CE that declining above 0.06 mol/L was highly likely because the thicker films reduced the fraction of inserted charge that actually switched active sites, lowering the optical change per unit charge [58].

Fig. 10 illustrates the coloring (t_c) and bleaching times (t_b) of the ITO/ V_2O_5 /electrolyte/ITO EC devices at various concentrations, revealing that as the sol-gel concentration increases, the t_c and t_b rise. This trend was similar to that observed for switching time, crystallinity, and film thickness, suggesting a correlation among these properties. Table 6 then compiles all data regarding t_c , t_b , OD, and CE of these ITO/ V_2O_5 /electrolyte/ITO EC devices. Results indicated that the CE increased with concentration and saturated at $27.9 \text{ cm}^2 \text{ C}^{-1}$ for the ITO/0.06 V_2O_5 /electrolyte/ITO device. This observation could be attributed to surface cracks due to increased agglomeration and faster evaporation rates during the sol-gel annealing process [59].

The observation revealed a significant increase in switching time from ITO/0.08 V_2O_5 /electrolyte/ITO to ITO/0.10 V_2O_5 /electrolyte/ITO devices, which was demonstrated by the rise in t_c and t_b of 7 s to 18 s and

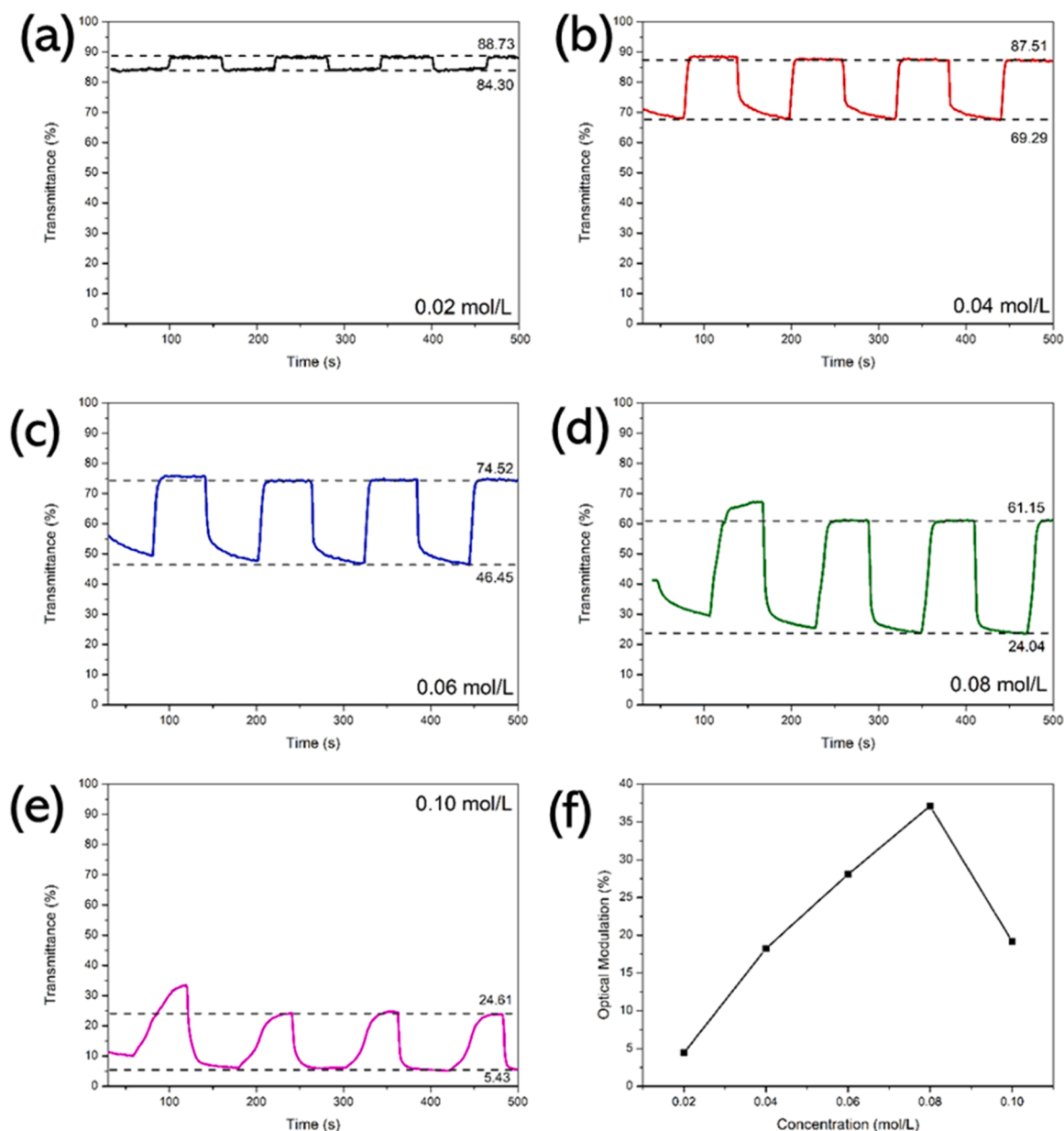


Fig. 8. (a) The transmittance responses of the (a) ITO/0.02 V₂O₅/electrolyte/ITO, (b) ITO/0.04 V₂O₅/electrolyte/ITO, (c) ITO/0.06 V₂O₅/electrolyte/ITO, (d) ITO/0.08 V₂O₅/electrolyte/ITO, and (e) ITO/0.10 V₂O₅/electrolyte/ITO EC devices. (f) The OM values of the ITO/V₂O₅/electrolyte/ITO EC devices at various concentrations.

Table 5

Summary of the coloring and bleaching transmittances of the ITO/V₂O₅/electrolyte/ITO EC devices 0.02 mol/L to 0.10 mol/L.

Device	T_c (%)	T_b (%)	ΔT (%)
ITO/0.02 V ₂ O ₅ /electrolyte/ITO	84.30	88.73	4.43
ITO/0.04 V ₂ O ₅ /electrolyte/ITO	69.29	87.51	18.22
ITO/0.06 V ₂ O ₅ /electrolyte/ITO	46.45	74.52	28.07
ITO/0.08 V ₂ O ₅ /electrolyte/ITO	24.04	61.15	37.11
ITO/0.10 V ₂ O ₅ /electrolyte/ITO	5.43	24.61	19.18

14 s to 31.9 s, respectively. This finding was ascribed to the higher crystallinity and roughness at higher concentrations, hindering ion insertion and extraction [47,48]. The result was probably due to the higher sol concentration, which gave rise to a thicker, more crystalline film, increasing the pathways for ion insertion or extraction and slowing the kinetics.

In earlier studies, slower Li⁺ diffusion kinetics were reported with high crystallinity V₂O₅ films containing denser packing and lower defect density. Hence, the effective diffusion path length was extended, alongside restricting the number of ion intercalation sites. This process could then lead to longer durations for both colouring and bleaching processes, as observed with ITO/0.10 V₂O₅/electrolyte/ITO [60,61]. Conversely, the ITO/0.02 V₂O₅/electrolyte/ITO and ITO/0.04 V₂O₅/electrolyte/ITO had the lowest t_c and t_b of 6.2 s or 1.2 s and 1.23 s or 4 s, respectively. This observation could be attributed to a more amorphous structure at lower concentrations, facilitating faster ion insertion and removal [48].

From the CV measurements, D_c represented the local ionic mobility present within the V₂O₅ films when subjected to minor perturbations (see Fig. 7). Nevertheless, the overall switching kinetics at the device level were indicated by t_c and t_b values (see Fig. 10), which could be further affected by various factors [62,63]. Such examples of these factors entailed thickness, crystallinity, and the distance of ion

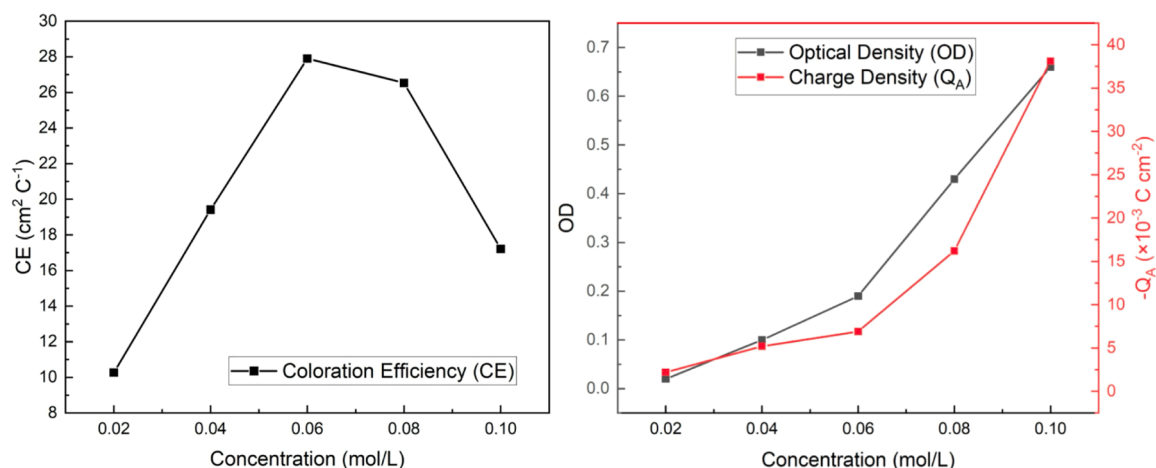


Fig. 9. (a) The CE and (b) optical and charge density of the ITO/ V_2O_5 /electrolyte/ITO EC devices at 0.02 mol/L to 0.10 mol/L.

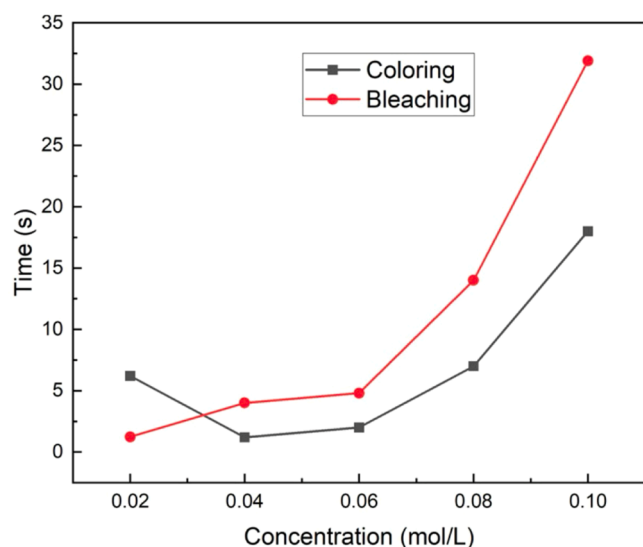


Fig. 10. The t_c and t_b values of ITO/ V_2O_5 /electrolyte/ITO EC devices at 0.02 mol/L to 0.10 mol/L.

Table 6

Summary of the coloring and bleaching kinetics of ITO/ V_2O_5 /electrolyte/ITO EC devices at 0.02 mol/L to 0.10 mol/L.

Device	t_c (s)	t_b (s)	ΔOD	$Q_A (\times 10^{-3} \text{ C cm}^{-2})$	CE ($\text{cm}^2 \text{ C}^{-1}$)
ITO/0.02 V_2O_5 /electrolyte/ITO	6.2	1.23	0.0222	2.2	10.27
ITO/0.04 V_2O_5 /electrolyte/ITO	1.2	4	0.101	5.2	19.42
ITO/0.06 V_2O_5 /electrolyte/ITO	2	4.8	0.192	6.9	27.9
ITO/0.08 V_2O_5 /electrolyte/ITO	7	14	0.43	16.2	26.53
ITO/0.10 V_2O_5 /electrolyte/ITO	18	31.9	0.656	38.1	17.21

transport. As such, films that were thicker and more crystalline might demonstrate extended switching times. This outcome could be attributed to the longer diffusion path lengths and interfacial resistance [60].

In order to substantiate the choice of 0.08 mol/L as the most effective concentration, a multi-parameter spider plot is illustrated in Fig. 11. All parameters (OM, CE, t_c , t_b , OD, and Q_A) were normalized to facilitate

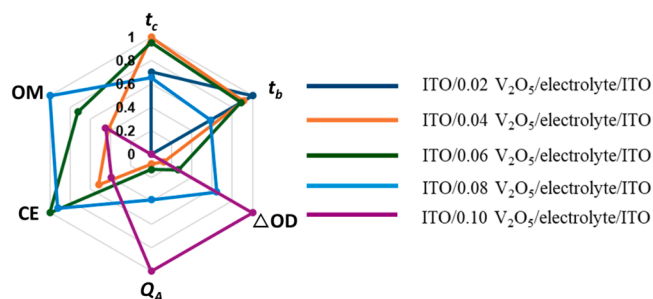


Fig. 11. The spider plot comparing EC performance parameters of ITO/ V_2O_5 /electrolyte/ITO EC devices at 0.02 mol/L to 0.10 mol/L concerning OM, OD, CE, t_c , t_b , and Q_A . The t_c and t_b values are inversely normalized so that larger radial values represent improved performance. All parameters are also scaled to the range 0–1 using min-max normalization.

direct comparison. Although ITO/0.10 V_2O_5 /electrolyte/ITO demonstrated larger Q_A and OD, it revealed a relative increase in switching times, alongside small CE. Therefore, at higher concentrations, the increased film thickness could compromise overall EC performance [62]. Conversely, ITO/0.80 V_2O_5 /electrolyte/ITO exhibited the most balanced performance among all parameters, strengthening its classification as the best concentration.

Overall, comparing all devices revealed that the ITO/0.08 V_2O_5 /electrolyte/ITO device possessed the most optimal potential. This conclusion was based on the optimized values for OM (37.11%), CE ($26.53 \text{ cm}^2 \text{ C}^{-1}$), OD (0.43), t_c (7 s), and t_b (14 s) observed in this device. Nonetheless, further analysis was still required to validate these outcomes. Several limitations still need to be addressed to understand the potential of V_2O_5 -based devices, including the limited range of sol concentrations, long-term stability analysis, and in-depth oxidation state analysis.

From these observations, ITO/0.08 V_2O_5 /electrolyte/ITO was selected for the stability measurements. In Fig. 12, the temporal transmittance response of ITO/0.08 V_2O_5 /electrolyte/ITO is depicted. During periodic switching, the stability measurements were conducted over 6000 s (50 coloration-bleaching cycles, 120 s each cycle). Initially, the device demonstrated significant initial EC activity, achieving an OM = ~30% (~16 cycles). Nonetheless, ongoing cycling then led to a gradual decrease in OM, suggesting a constrained level of cycling stability. This degradation could be linked to ion trapping and structural fatigue resulting from the repeated intercalation and deintercalation of Li^+ within the V_2O_5 lattice.

Even though extended endurance testing is frequently documented

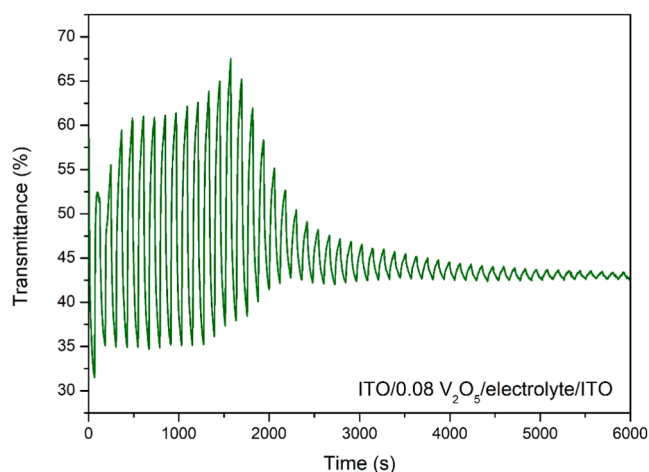


Fig. 12. The stability for ITO/0.08 V₂O₅/electrolyte/ITO, indicating coloring and bleaching transmittances utilising CA.

for highly stable EC systems (WO₃) [64], this study emphasized the intrinsic cycling behavior of pure V₂O₅ films. Fig. 12 illustrates that the device demonstrates significant degradation during the initial 50 cycles, a behavior typical of undoped V₂O₅, as extensively documented in existing studies [45,65]. Thus, the observed instability underscored the importance of employing material engineering strategies. For instance, the incorporation of dopants (Ti) enhanced the structural integrity of V₂O₅, alongside mitigating degradation throughout the cycling process [66]. Another study introduced controlled vacancy defects to enhance both the EC performance and stability of materials [67]. In a separate work, combining V₂O₅ with WO₃, which utilized the strong lattice framework of WO₃, could optimize ion insertion pathways [68].

In this study, the EC performance was significantly associated with the V⁴⁺/V⁵⁺ redox couple. Nonetheless, X-ray photoelectron spectroscopy (XPS) measurements were not carried out because of limitations related to the instrumentation access. Rather, the examination of changes in oxidation states relies on indirect evidence derived from electrochemical behaviour, OM, and structural evolution. This study then proposed that future studies should further improve the V₂O₅-based EC devices in terms of repeatability, stability, and reproducibility, alongside XPS analysis.

3.5. Comparison of ITO/V₂O₅/electrolyte/ITO EC devices with literature

In Table 7, a comparison of EC performance of the optimised ITO/0.08 V₂O₅/electrolyte/ITO device, alongside representative V₂O₅- and WO₃-based systems, is demonstrated, which are documented in recent literature. Although doped and composite systems demonstrated elevated CE values, the device discussed in this study showcased competitive performance among undoped V₂O₅ films, all while preserving a balanced approach to OM and switching kinetics. As such, this comparison underscored the efficacy of optimising concentration without altering the composition. It should also be noted that in this study, the impact of sol-gel precursor concentration using undoped V₂O₅ was focused, rather than on maximizing absolute performance through compositional modification or complex architectures.

4. Conclusions

This study successfully investigated the effects of V₂O₅ concentration (0.02 mol/L to 0.10 mol/L) on the performance of EC devices. Unlike previous research that primarily examined V₂O₅ thin films, the analysis in this experiment was extended to fully assembled EC devices. By comparing the series of devices, the EC device that balanced between OM, CE, and switching time was observed for the ITO/0.08 V₂O₅/

Table 7

Comparison summary of various EC parameters for representative V₂O₅- and WO₃-based EC devices reported in selected studies.

Material/Device	CE (cm ² C ⁻¹)	OM/ Δ T (%)	t _c /t _b (s)	Reference
V ₂ O ₅ (annealed 200 °C)	34.93	42.32	0.4/3	[69]
V ₂ O ₅ with oxygen-vacancy nanosheets	96.23	-	3.32/3.39	[67]
Ag-decorated V ₂ O ₅	93.7	51.7	9.4/13.6	[70]
Ti-doped V ₂ O ₅	95.7	51.1	5/6	[71]
Ti ⁴⁺ -doped V ₂ O ₅ film	34.15	-	9/-	[65]
WO ₃ nanosheet/ITO composite	154.16	88	-	[72]
WO ₃ @PEO fibrous	61.3	-	1.6/-	[73]
WO ₃ (pH-tuned film)	122.2	30	1.10/1	[74]
This study	26.53	37.11	7/14	-

electrolyte/ITO device. The findings could then provide valuable information for improving V₂O₅-based EC device performance in future applications. Future studies should involve further analyzing these devices through in-depth tests related to V⁴⁺/V⁵⁺ redox couple reactions, alongside improving the stability.

CRediT authorship contribution statement

Faisal Abdullah Sadeq: Methodology, Investigation, Formal analysis, Data curation. **Pei-Ling Low:** Visualization, Supervision, Resources, Project administration, Funding acquisition. **Tan Kar:** Writing – review & editing, Visualization, Validation. **Zhang-Xuan Cheng:** Writing – original draft, Software, Methodology, Investigation, Formal analysis, Data curation. **Ming-Yue Tan:** Methodology, Investigation, Formal analysis. **Cheikh Zakaria Eldjilali:** Methodology, Investigation, Formal analysis. **Ebrahim Abdelhamed Abdelrahman:** Methodology, Investigation, Formal analysis. **Kah-Yoong Chan:** Writing – review & editing, Visualization, Validation, Supervision, Resources, Project administration, Investigation, Funding acquisition, Formal analysis, Conceptualization. **Thien Gregory:** Writing – original draft, Software, Methodology, Investigation, Formal analysis, Data curation.

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Declaration of Competing Interest

The authors declare the following financial interests/personal relationships which may be considered as potential competing interests: Kah-Yoong Chan reports financial support was provided by Universiti Multimedia - Kampus Cyberjaya. If there are other authors, they declare that they have no known competing financial interests or personal relationships that could have appeared to influence the work reported in this paper.

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Data availability

Data will be made available on request.

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